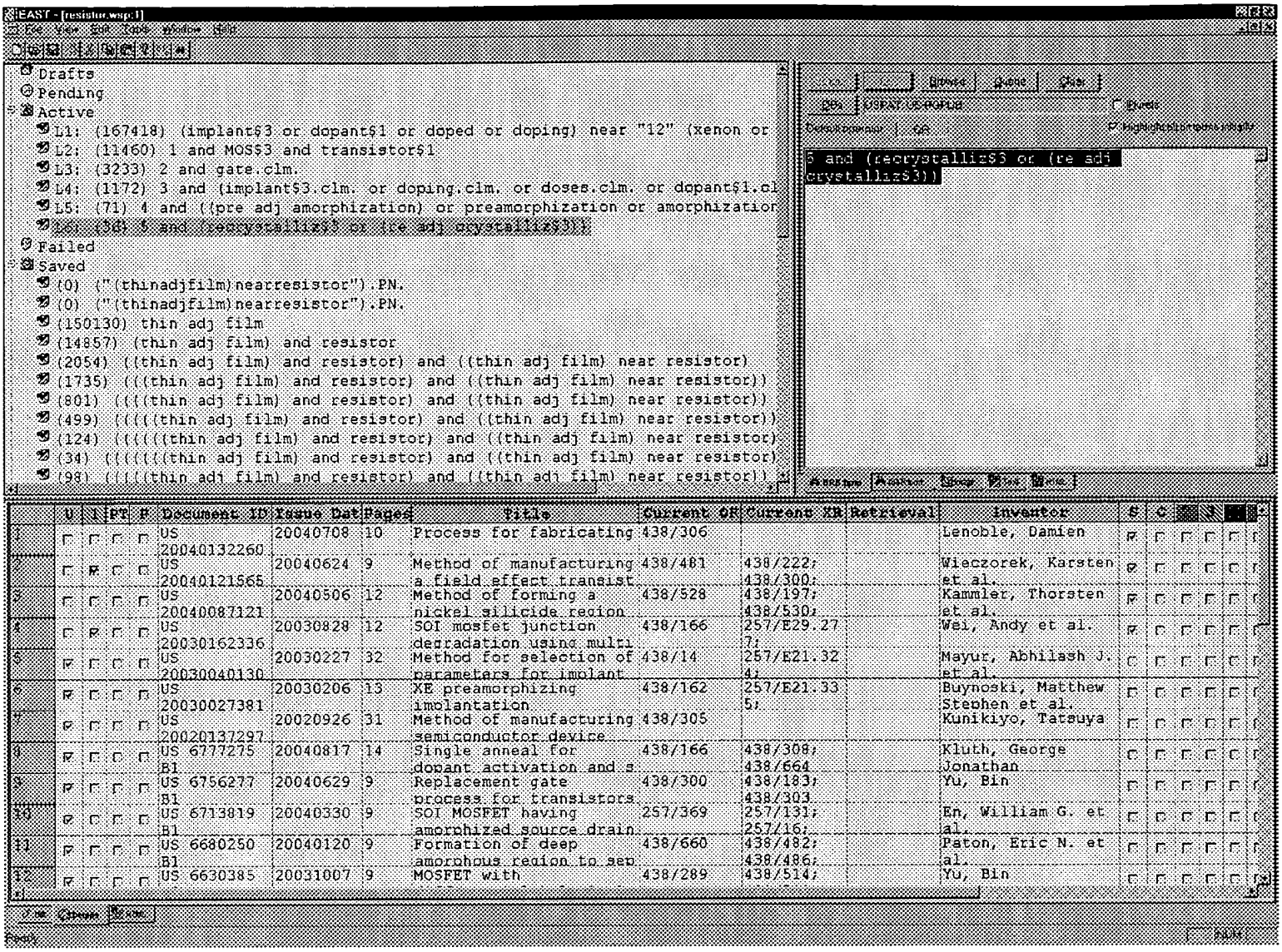
EAST - [resistor.wsp:1]
File View Edit Tools Window Help
Drafts
Pending
Active
L1: (167418) (implant$3 or dopant$1 or doped or doping) near "12" (xenon or
L2: (11460) 1 and MOS$3 and transistor$1
L3: (3233) 2 and gate.clm.
L4: (1172) 3 and (implant$3.clm. or doping.clm. or doses.clm. or dopant$1.cl
L5: (71) 4 and ((pre adj amorphization) or preamorphization or amorphizatior
L6: (36) 5 and (recrystallize$3 or (re adj crystallize$3))
Failed
Saved
(0) ("(thinadjfilm)nearresistor").PN.
(0) ("(thinadjfilm)nearresistor").PN.
(150130) thin adj film
(14857) (thin adj film) and resistor
(2054) ((thin adj film) and resistor) and ((thin adj film) near resistor)
(1735) (((thin adj film) and resistor) and ((thin adj film) near resistor))
(801) ((((thin adj film) and resistor) and ((thin adj film) near resistor))
(499) (((((thin adj film) and resistor) and ((thin adj film) near resistor))
(124) ((((((thin adj film) and resistor) and ((thin adj film) near resistor)
(34) (((((((thin adj film) and resistor) and ((thin adj film) near resistor)
(98) ((((thin adj film) and resistor) and ((thin adj film) near resistor))
5 and (recrystallize$3 or (re adj crystallize$3))

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	E	C	3
1	☐	☐	☐	☐	US 20040132260	20040708	10	Process for fabricating	438/306			Lenoble, Damien	☑	☐	☐
2	☐	☑	☐	☐	US 20040121565	20040624	9	Method of manufacturing a field effect transist	438/481	438/222; 438/300;		Wieczorek, Karsten et al.	☑	☐	☐
3	☐	☐	☐	☐	US 20040087121	20040506	12	Method of forming a nickel silicide region	438/528	438/197; 438/530;		Kammler, Thorsten et al.	☑	☐	☐
4	☐	☑	☐	☐	US 20030162336	20030828	12	SOI mosfet junction degradation using multi	438/166	257/E29.27 7;		Wei, Andy et al.	☑	☐	☐
5	☑	☐	☐	☐	US 20030040130	20030227	32	Method for selection of parameters for implant	438/14	257/E21.32 4;		Mayur, Abhilash J. et al.	☐	☐	☐
6	☑	☐	☐	☐	US 20030027381	20030206	13	XE preamorphizing implantation	438/162	257/E21.33 5;		Buynoski, Matthew Stephen et al.	☐	☐	☐
7	☑	☐	☐	☐	US 20020137297	20020926	31	Method of manufacturing semiconductor device	438/305			Kunikiyo, Tatsuya	☐	☐	☐
8	☑	☐	☐	☐	US 6777275 B1	20040817	14	Single anneal for dopant activation and s	438/166	438/308; 438/664		Kluth, George Jonathan	☐	☐	☐
9	☑	☐	☐	☐	US 6756277 B1	20040629	9	Replacement gate process for transistors	438/300	438/183; 438/303		Yu, Bin	☐	☐	☐
10	☑	☐	☐	☐	US 6713819 B1	20040330	9	SOI MOSFET having amorphized source drain	257/369	257/131; 257/16;		En, William G. et al.	☐	☐	☐
11	☑	☐	☐	☐	US 6680250 B1	20040120	9	Formation of deep amorphous region to sep	438/660	438/482; 438/486;		Paton, Eric N. et al.	☐	☐	☐
12	☑	☐	☐	☐	US 6630385	20031007	9	MOSFET with	438/289	438/514;		Yu, Bin	☐	☐	☐